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2N5457, 2N5458

JFETs - General Purpose

N-Channel – Depletion

N-Channel Junction Field Effect Transistors, depletion mode (Type A) designed for audio and switching applications.

Features

- N-Channel for Higher Gain
- Drain and Source Interchangeable
- High AC Input Impedance
- High DC Input Resistance
- Low Transfer and Input Capacitance
- Low Cross-Modulation and Intermodulation Distortion
- Plastic Encapsulated Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS

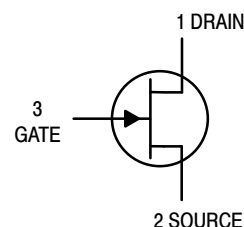
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	-25	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	310 2.82	mW mW/ $^\circ\text{C}$
Operating Junction Temperature	T_J	135	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

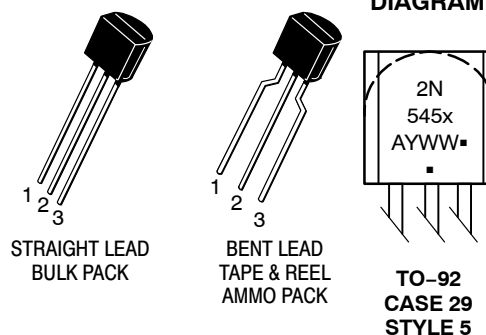


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MARKING DIAGRAM



2N545x = Device Code
x = 7 or 8

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
2N5457	TO-92	1000 Units/Box
2N5457G	TO-92 (Pb-Free)	1000 Units/Box
2N5458	TO-92	1000 Units/Box
2N5458G	TO-92 (Pb-Free)	1000 Units/Box

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N5457, 2N5458

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate–Source Breakdown Voltage ($I_G = -10\ \mu\text{Adc}$, $V_{DS} = 0$)		$V_{(BR)GSS}$	-25	–	–	Vdc
Gate Reverse Current ($V_{GS} = -15\ \text{Vdc}$, $V_{DS} = 0$) ($V_{GS} = -15\ \text{Vdc}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$)		I_{GSS}	– –	– –	-1.0 -200	nAdc
Gate–Source Cutoff Voltage ($V_{DS} = 15\ \text{Vdc}$, $i_D = 10\ \text{nAdc}$)	2N5457 2N5458	$V_{GS(off)}$	-0.5 -1.0	– –	-6.0 -7.0	Vdc
Gate–Source Voltage ($V_{DS} = 15\ \text{Vdc}$, $i_D = 100\ \mu\text{Adc}$) ($V_{DS} = 15\ \text{Vdc}$, $i_D = 200\ \mu\text{Adc}$)	2N5457 2N5458	V_{GS}	– –	-2.5 -3.5	– –	Vdc
ON CHARACTERISTICS						
Zero–Gate–Voltage Drain Current (Note 1) ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$)	2N5457 2N5458	I_{DSS}	1.0 2.0	3.0 6.0	5.0 9.0	mAdc
DYNAMIC CHARACTERISTICS						
Forward Transfer Admittance (Note 1) ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1\ \text{kHz}$)	2N5457 2N5458	$ Y_{fs} $	1000 1500	3000 4000	5000 5500	μmhos
Output Admittance Common Source (Note 1) ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1\ \text{kHz}$)		$ Y_{os} $	–	10	50	μmhos
Input Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1\ \text{kHz}$)		C_{iss}	–	4.5	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1\ \text{kHz}$)		C_{rss}	–	1.5	3.0	pF

1. Pulse Width $\leq 630\ \text{ms}$, Duty Cycle $\leq 10\%$.

2N5457, 2N5458

TYPICAL CHARACTERISTICS For 2N5457 Only

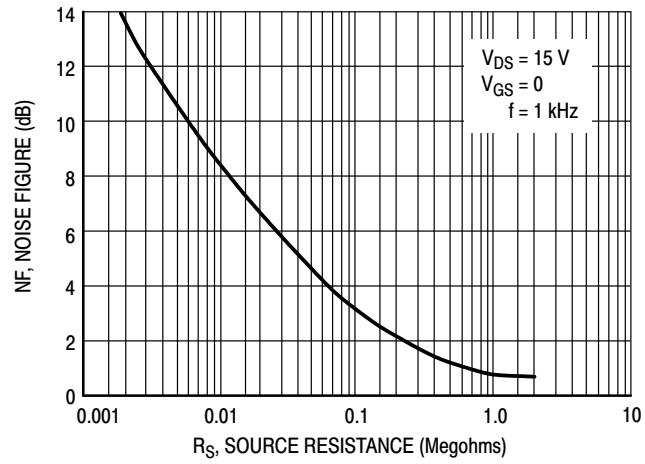


Figure 1. Noise Figure versus Source Resistance

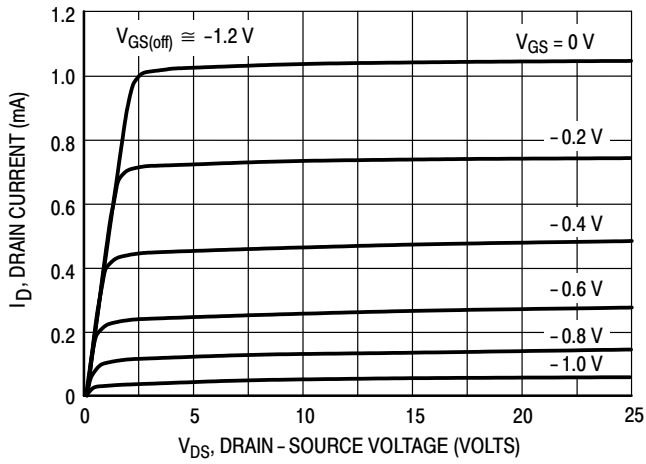


Figure 2. Typical Drain Characteristics

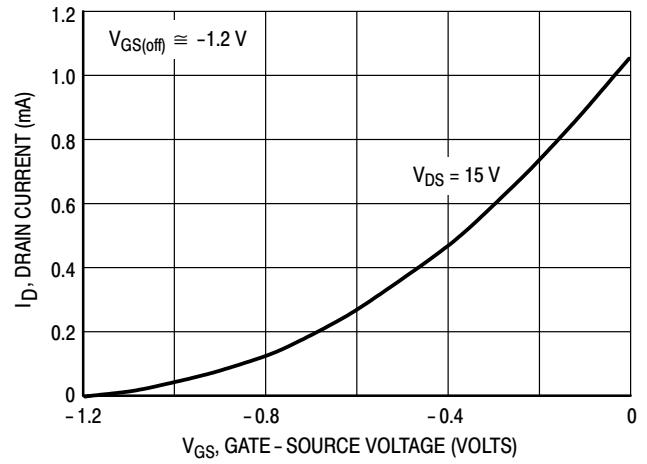


Figure 3. Common Source Transfer Characteristics

2N5457, 2N5458

TYPICAL CHARACTERISTICS For 2N5457 Only

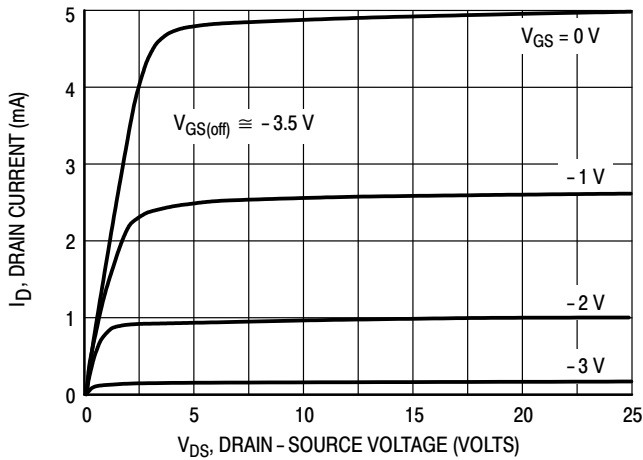


Figure 4. Typical Drain Characteristics

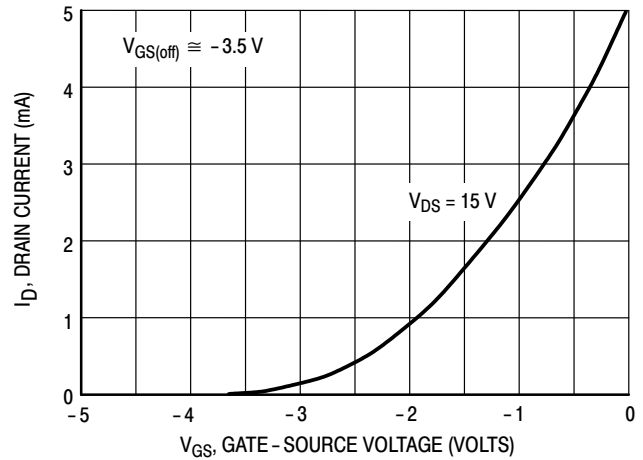


Figure 5. Common Source Transfer Characteristics

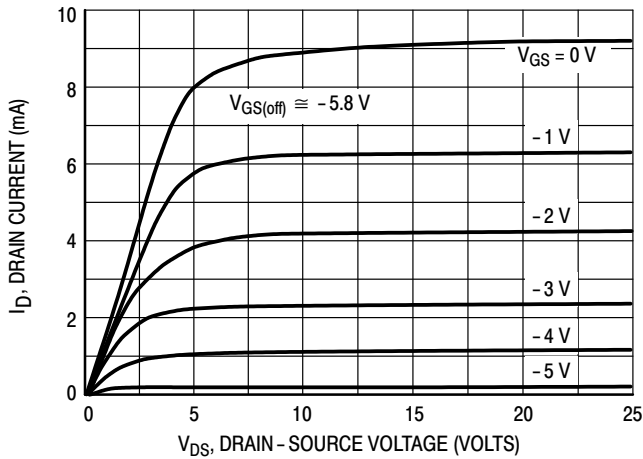


Figure 6. Typical Drain Characteristics

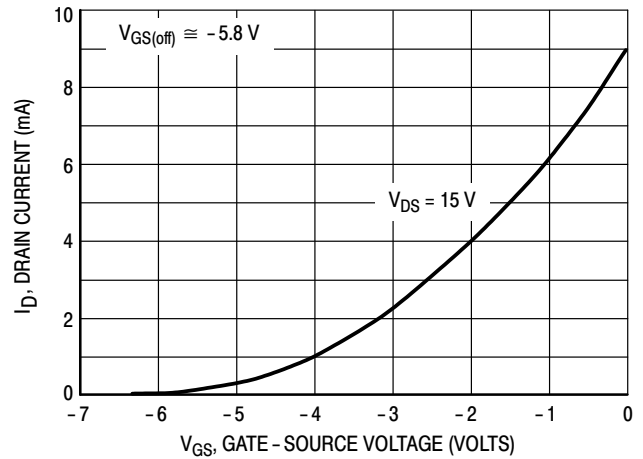


Figure 7. Common Source Transfer Characteristics

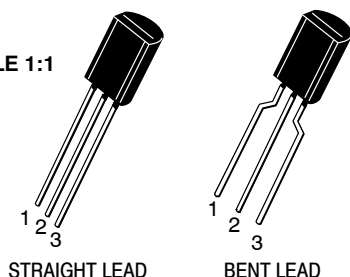
NOTE: Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS} .

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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ON

SCALE 1:1

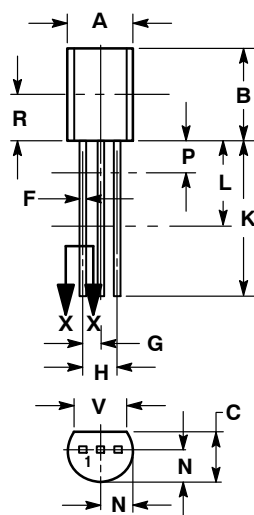


STRAIGHT LEAD

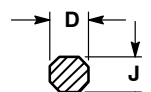
BENT LEAD

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CASE 29-10
ISSUE A

DATE 08 MAY 2012



STRAIGHT LEAD

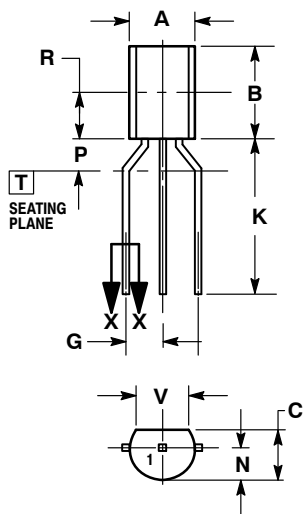


SECTION X-X

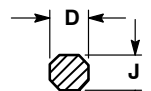
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



BENT LEAD



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
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STYLES ON PAGE 2

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CASE 29-10
ISSUE A

DATE 08 MAY 2012

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STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V _{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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